

# 74LV125

Quad buffer/line driver; 3-state

Rev. 03 — 7 April 2009

Product data sheet

## 1. General description

The 74LV125 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC125 and 74HCT125.

The 74LV125 provides four non-inverting buffer/line drivers with 3-state outputs. The 3-state outputs ( $nY$ ) are controlled by the output enable input ( $n\overline{OE}$ ). A HIGH at  $n\overline{OE}$  causes the outputs to assume a high-impedance OFF-state.

## 2. Features

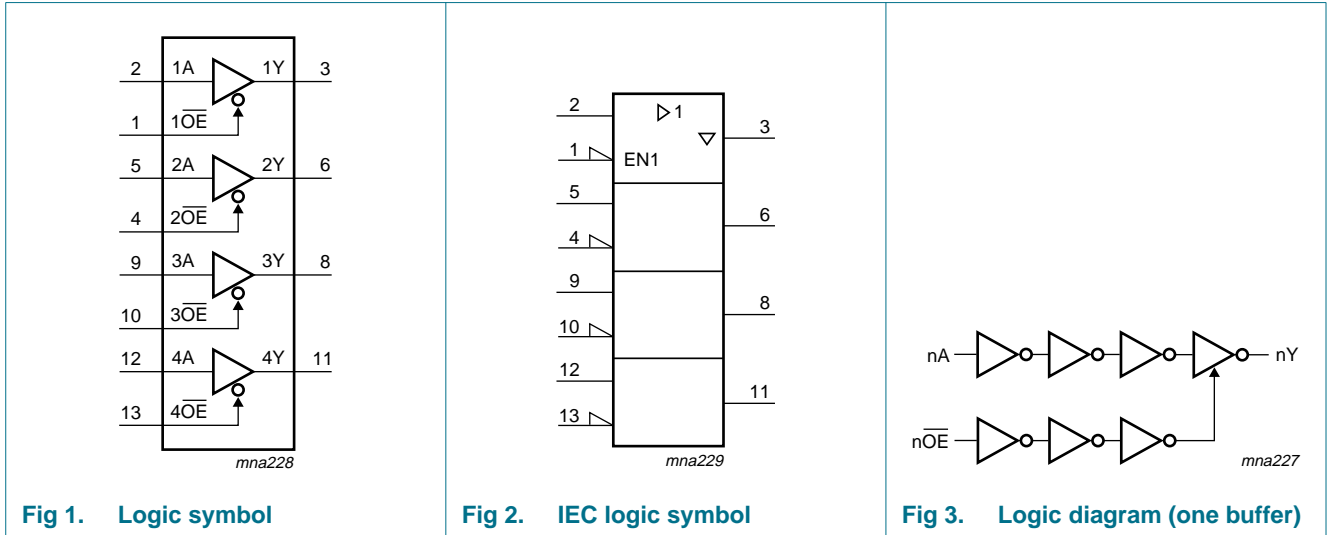
- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between  $V_{CC} = 2.7$  V and  $V_{CC} = 3.6$  V
- Typical output ground bounce < 0.8 V at  $V_{CC} = 3.3$  V and  $T_{amb} = 25$  °C
- Typical HIGH-level output voltage ( $V_{OH}$ ) undershoot: > 2 V at  $V_{CC} = 3.3$  V and  $T_{amb} = 25$  °C
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from  $-40$  °C to  $+85$  °C and from  $-40$  °C to  $+125$  °C

## 3. Ordering information

Table 1. Ordering information

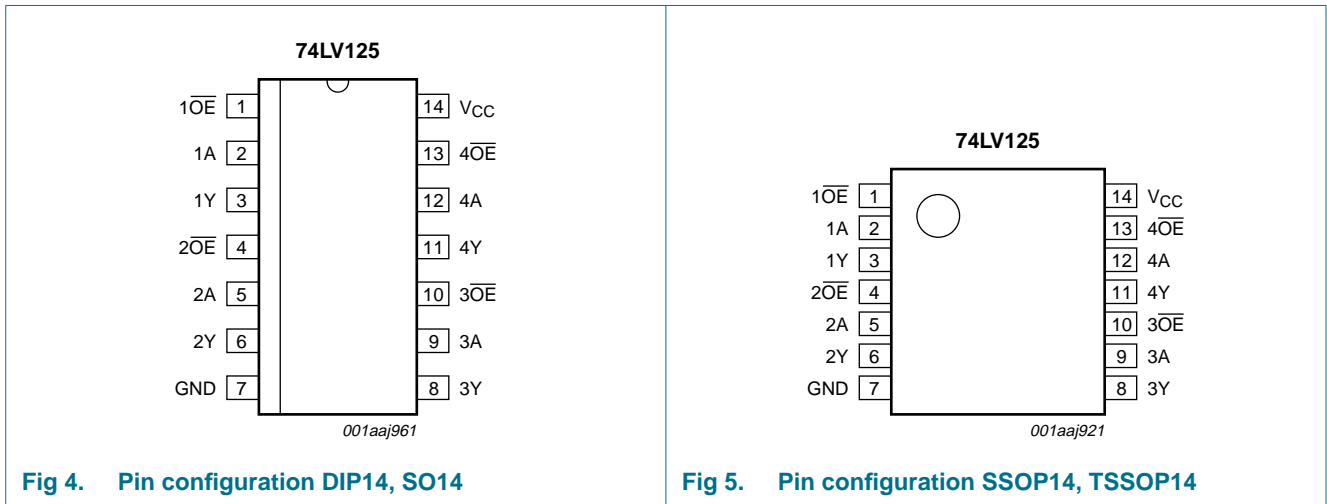
Type number	Package			
	Temperature range	Name	Description	Version
74LV125N	$-40$ °C to $+125$ °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74LV125D	$-40$ °C to $+125$ °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LV125DB	$-40$ °C to $+125$ °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74LV125PW	$-40$ °C to $+125$ °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1

4. Functional diagram



5. Pinning information

5.1 Pinning



## 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{1OE}$ , $\overline{2OE}$ , $\overline{3OE}$ , $\overline{4OE}$ ,	1, 4, 10, 13	output enable input (active LOW)
1A, 2A, 3A, 4A	2, 5, 9, 12	data input
1Y, 2Y, 3Y, 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
$V_{CC}$	14	supply voltage

## 6. Functional description

Table 3. Function table<sup>[1]</sup>

Control	Input	Output
$\overline{nOE}$	nA	nY
L	L	L
L	H	H
H	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$I_{IK}$	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
$I_{OK}$	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	[1] -	±50	mA
$I_O$	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	-	±35	mA
$I_{CC}$	supply current		-	70	mA
$I_{GND}$	ground current		-70	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$	[2]		
		DIP14	-	750	mW
		SO14, SSOP14, TSSOP14	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For DIP14 packages: above 70 °C the value of  $P_{tot}$  derates linearly with 12 mW/K.  
 For SO14 packages: above 70 °C the value of  $P_{tot}$  derates linearly with 8 mW/K.  
 For (T)SSOP14 packages: above 60 °C the value of  $P_{tot}$  derates linearly with 5.5 mW/K.

## 8. Recommended operating conditions

**Table 5. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC}$	supply voltage <sup>[1]</sup>		1.0	3.3	5.5	V
$V_I$	input voltage		0	-	$V_{CC}$	V
$V_O$	output voltage		0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.0\text{ V to }2.0\text{ V}$	-	-	500	ns/V
		$V_{CC} = 2.0\text{ V to }2.7\text{ V}$	-	-	200	ns/V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	100	ns/V
		$V_{CC} = 3.6\text{ V to }5.5\text{ V}$	-	-	50	ns/V

[1] The static characteristics are guaranteed from  $V_{CC} = 1.2\text{ V}$  to  $V_{CC} = 5.5\text{ V}$ , but LV devices are guaranteed to function down to  $V_{CC} = 1.0\text{ V}$  (with input levels GND or  $V_{CC}$ ).

## 9. Static characteristics

**Table 6. Static characteristics**

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 1.2\text{ V}$	0.9	-	-	0.9	-	V
		$V_{CC} = 2.0\text{ V}$	1.4	-	-	1.4	-	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	2.0	-	-	2.0	-	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 1.2\text{ V}$	-	-	0.3	-	0.3	V
		$V_{CC} = 2.0\text{ V}$	-	-	0.6	-	0.6	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	0.8	-	0.8	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$						
		$I_O = -100\ \mu\text{A}; V_{CC} = 1.2\text{ V}$	-	1.2	-	-	-	V
		$I_O = -100\ \mu\text{A}; V_{CC} = 2.0\text{ V}$	1.8	2.0	-	1.8	-	V
		$I_O = -100\ \mu\text{A}; V_{CC} = 2.7\text{ V}$	2.5	2.7	-	2.5	-	V
		$I_O = -100\ \mu\text{A}; V_{CC} = 3.0\text{ V}$	2.8	3.0	-	2.8	-	V
		$I_O = -100\ \mu\text{A}; V_{CC} = 4.5\text{ V}$	4.3	4.5	-	4.3	-	V
		$I_O = -8\text{ mA}; V_{CC} = 3.0\text{ V}$	2.4	2.82	-	2.2	-	V
$I_O = -16\text{ mA}; V_{CC} = 4.5\text{ V}$	3.6	4.2	-	3.5	-	V		

**Table 6. Static characteristics ...continued**

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 1.2 V	-	0	-	-	-	V
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 2.0 V	-	0	0.2	-	0.2	V
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 2.7 V	-	0	0.2	-	0.2	V
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 3.0 V	-	0	0.2	-	0.2	V
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 4.5 V	-	0	0.2	-	0.2	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 3.0 V	-	0.20	0.40	-	0.50	V
		I <sub>O</sub> = 16 mA; V <sub>CC</sub> = 4.5 V	-	0.35	0.55	-	0.65	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	1.0	-	1.0	μA
I <sub>OZ</sub>	OFF-state output current	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>O</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	5	-	10	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	20	-	160	μA
ΔI <sub>CC</sub>	additional supply current	per input; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	500	-	850	μA
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T<sub>amb</sub> = 25 °C.

## 10. Dynamic characteristics

**Table 7. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
t <sub>pd</sub>	propagation delay	nA to nY; see <a href="#">Figure 6</a> <sup>[2]</sup>						
		V <sub>CC</sub> = 1.2 V	-	55	-	-	-	ns
		V <sub>CC</sub> = 2.0 V	-	19	24	-	31	ns
		V <sub>CC</sub> = 2.7 V	-	14	18	-	23	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V; C <sub>L</sub> = 15 pF <sup>[3]</sup>	-	9	-	-	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V <sup>[3]</sup>	-	10	14	-	18	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	12	-	15	ns
t <sub>en</sub>	enable time	nOE to nY; see <a href="#">Figure 7</a> <sup>[2]</sup>						
		V <sub>CC</sub> = 1.2 V	-	75	-	-	-	ns
		V <sub>CC</sub> = 2.0 V	-	26	31	-	39	ns
		V <sub>CC</sub> = 2.7 V	-	19	23	-	29	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V <sup>[3]</sup>	-	14	18	-	23	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	15	-	19	ns

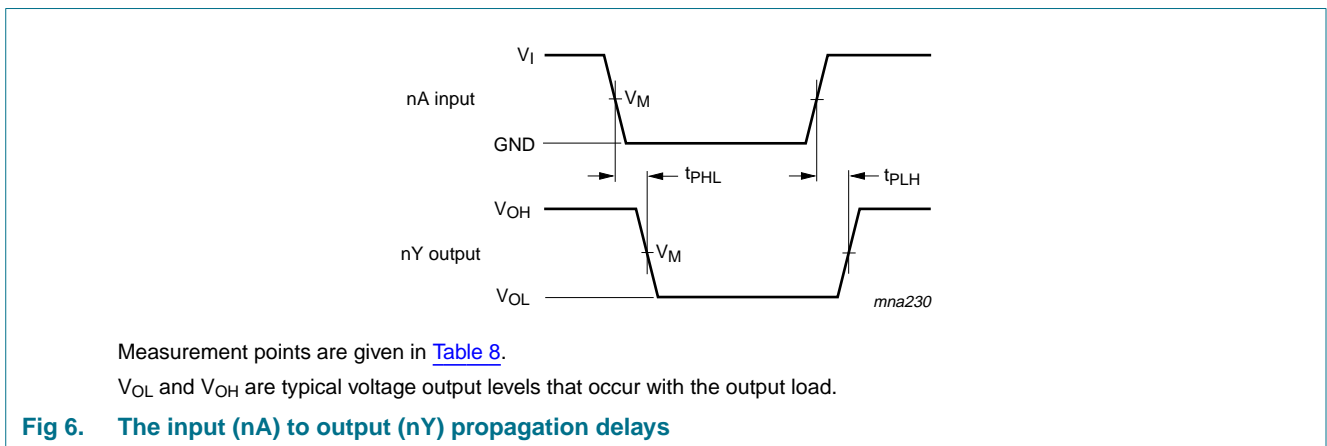
**Table 7. Dynamic characteristics ...continued**

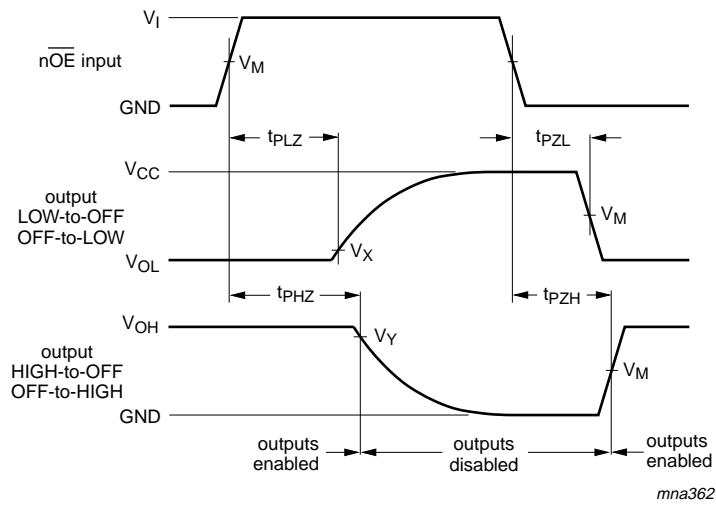
Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
t <sub>dis</sub>	disable time	nOE to nY; see <a href="#">Figure 7</a> <sup>[2]</sup>						
		V <sub>CC</sub> = 1.2 V	-	65	-	-	-	ns
		V <sub>CC</sub> = 2.0 V	-	24	32	-	39	ns
		V <sub>CC</sub> = 2.7 V	-	18	24	-	29	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V <sup>[3]</sup>	-	14	20	-	24	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	17	-	21	ns
C <sub>PD</sub>	power dissipation capacitance	C <sub>L</sub> = 50 pF; f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> ; V <sub>CC</sub> = 3.3 V <sup>[4]</sup>	-	22	-	-	-	pF

- [1] All typical values are measured at T<sub>amb</sub> = 25 °C.
- [2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.  
t<sub>en</sub> is the same as t<sub>PZL</sub> and t<sub>PZH</sub>.  
t<sub>dis</sub> is the same as t<sub>PLZ</sub> and t<sub>PHZ</sub>.
- [3] Typical values are measured at nominal supply voltage (V<sub>CC</sub> = 3.3 V).
- [4] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
P<sub>D</sub> = C<sub>PD</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>i</sub> × N + Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) where:  
f<sub>i</sub> = input frequency in MHz, f<sub>o</sub> = output frequency in MHz  
C<sub>L</sub> = output load capacitance in pF  
V<sub>CC</sub> = supply voltage in Volts  
N = number of inputs switching  
Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of the outputs.

## 11. Waveforms



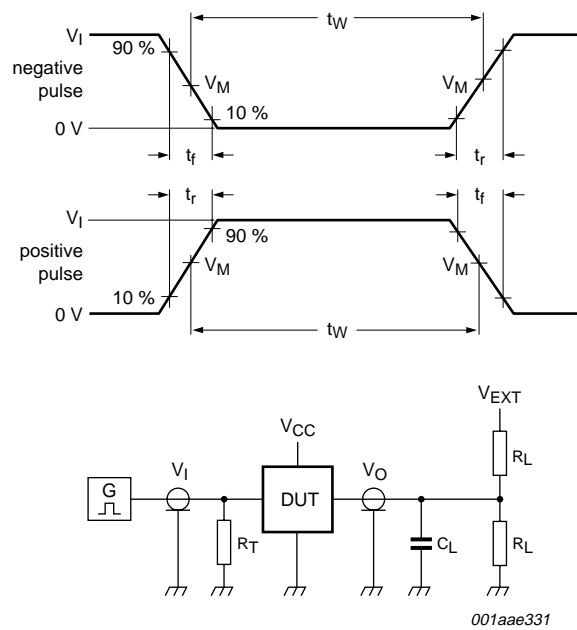


Measurement points are given in [Table 8](#).  
 $V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 7. Enable and disable times**

**Table 8. Measurement points**

Supply voltage	Input	Output		
$V_{CC}$	$V_M$	$V_M$	$V_X$	$V_Y$
< 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.1V_{CC}$	$V_{OH} - 0.1V_{CC}$
2.7 V to 3.6 V	1.5 V	1.5 V	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$
$\geq 4.5 V$	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.1V_{CC}$	$V_{OH} - 0.1V_{CC}$



Test data is given in [Table 9](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

**Fig 8. Load circuit for measuring switching times**

**Table 9. Test data**

Supply voltage	Input		Load		$V_{EXT}$		
$V_{CC}$	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
< 2.7 V	$V_{CC}$	$\leq 2.5$ ns	50 pF	1 k $\Omega$	open	GND	$2V_{CC}$
2.7 V to 3.6 V	2.7 V	$\leq 2.5$ ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$2V_{CC}$
$\geq 4.5$ V	$V_{CC}$	$\leq 2.5$ ns	50 pF	1 k $\Omega$	open	GND	$2V_{CC}$



12. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1

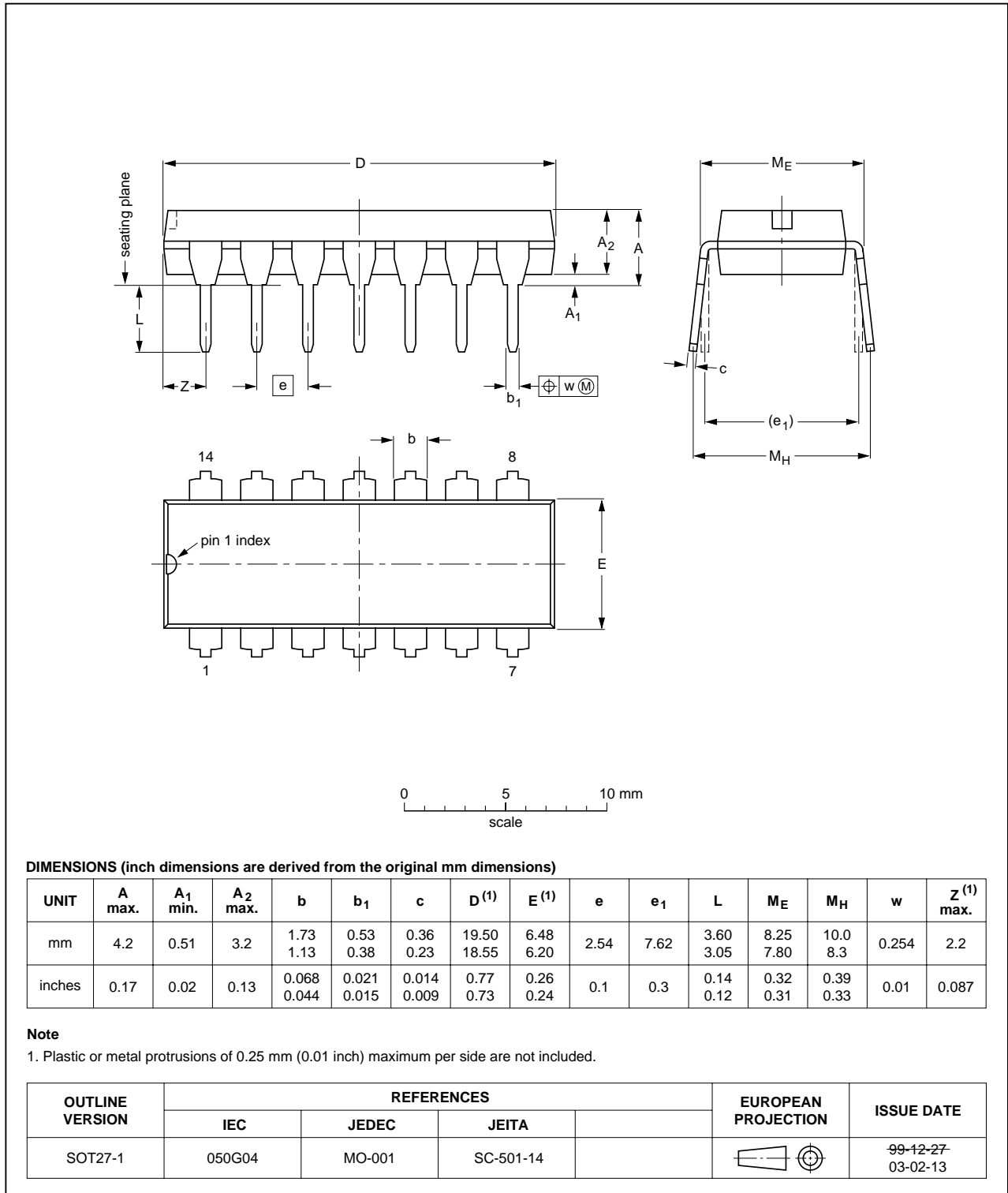


Fig 9. Package outline SOT27-1 (DIP14)

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

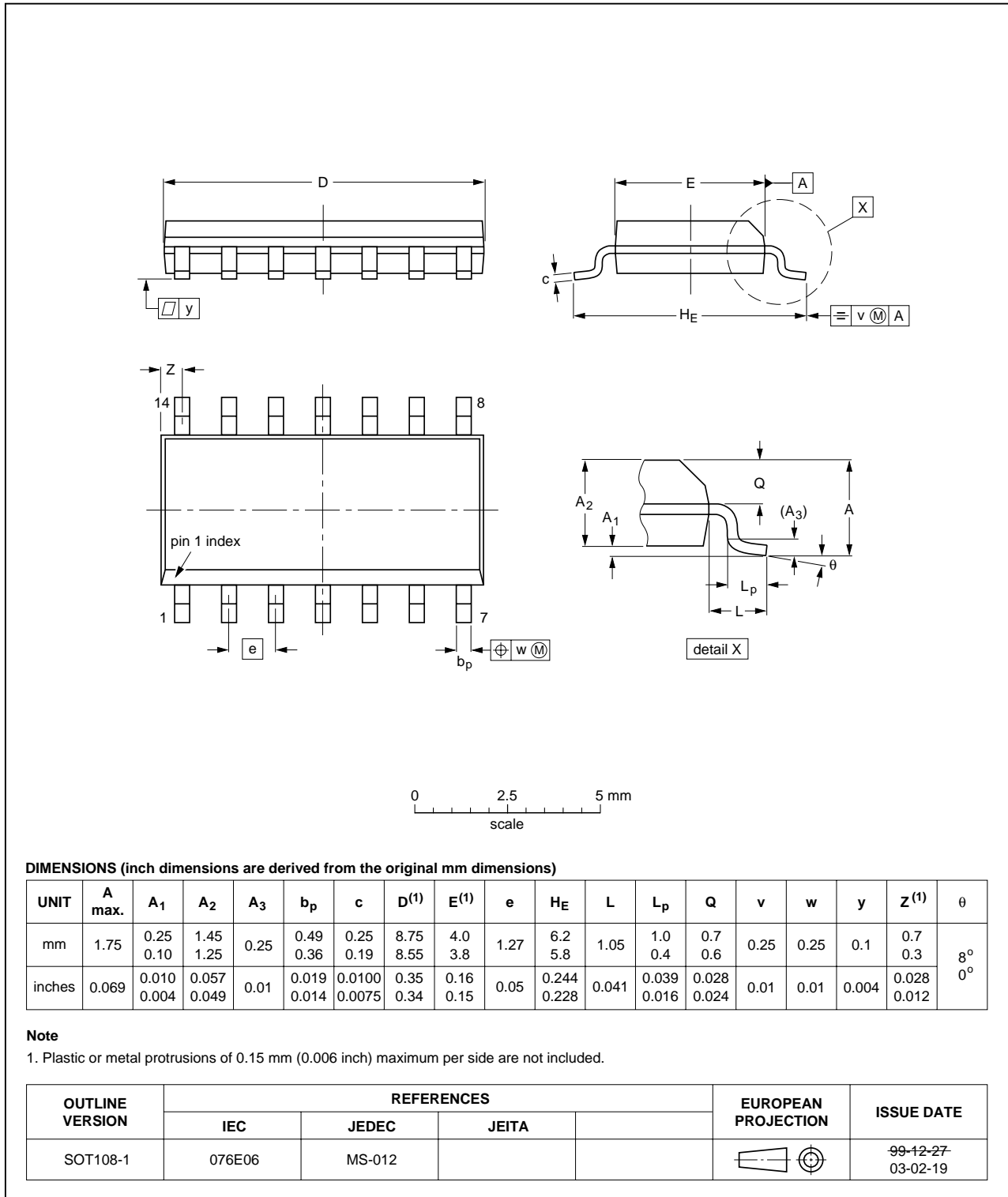


Fig 10. Package outline SOT108-1 (SO14)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1

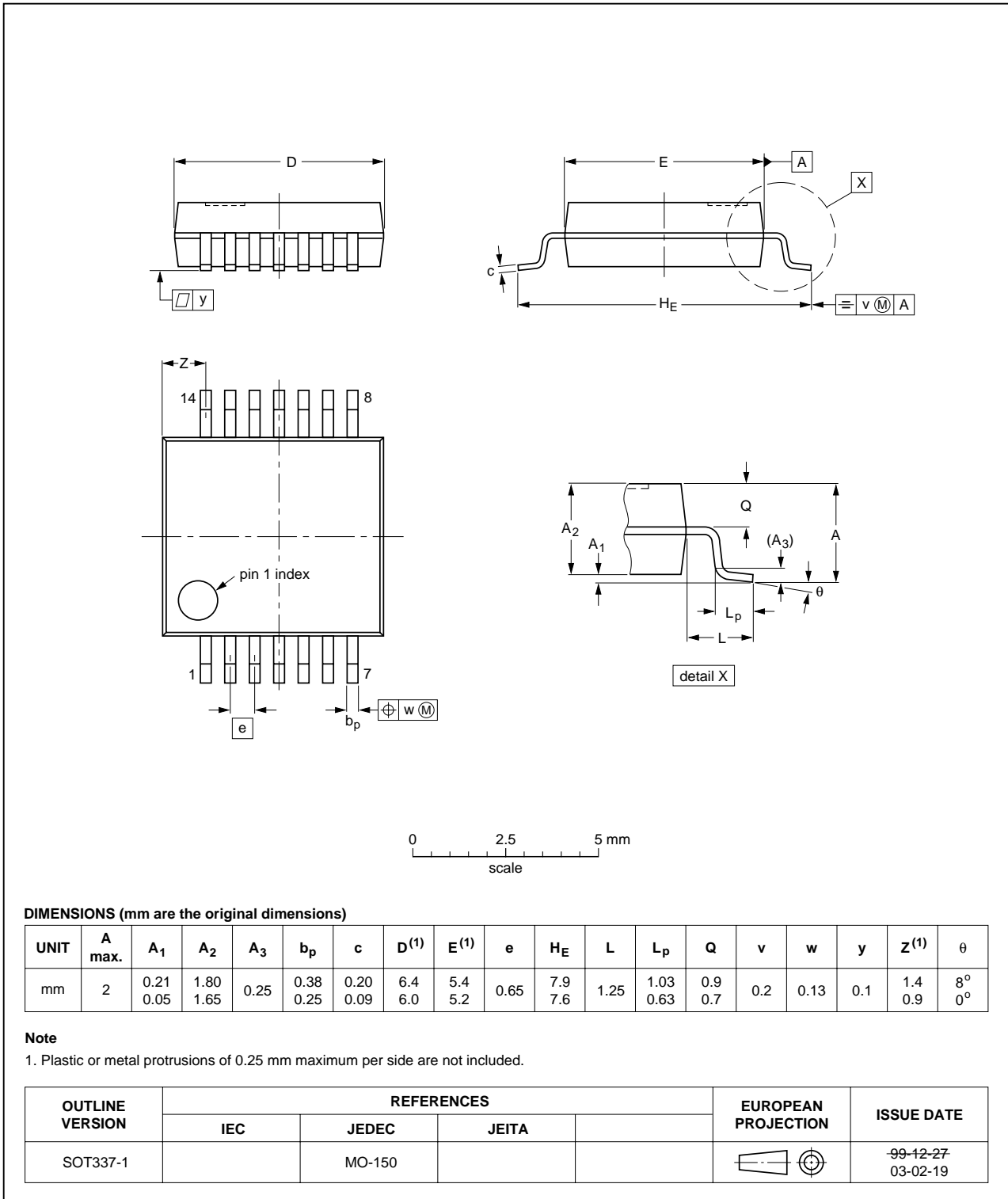


Fig 11. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

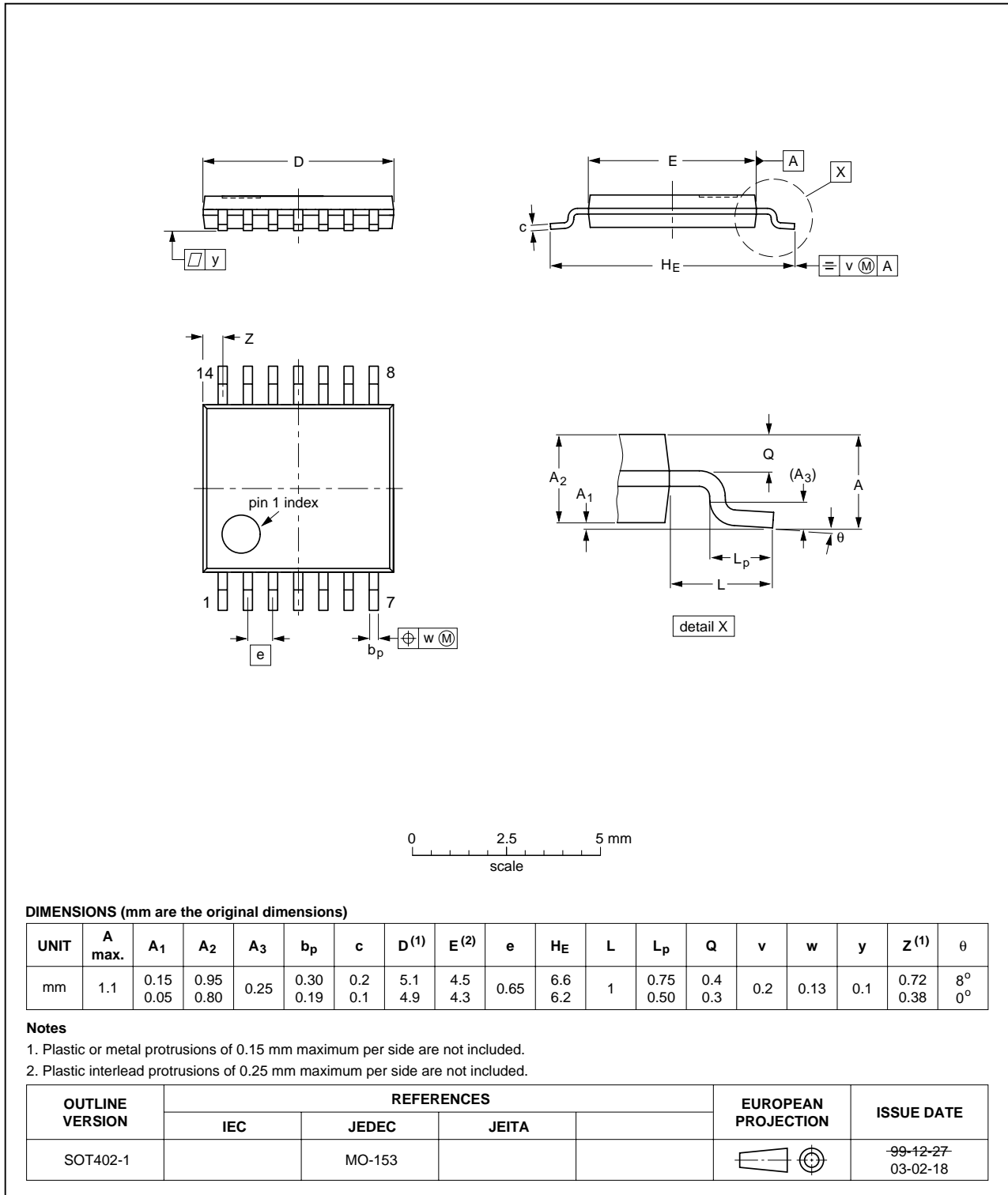


Fig 12. Package outline SOT402-1 (TSSOP14)

## 13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV125_3	20090407	Product data sheet	-	74LV125_2
Modifications:	<ul style="list-style-type: none"><li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>Legal texts have been adapted to the new company name when appropriate.</li></ul>			
74LV125_2	19980428	Product specification	-	74LV125_1
74LV125_1	19970203	Product specification	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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